

NPN Low Saturation Transistor

These devices are designed for high current gain and low saturation voltage with collector currents up to 3.0 A continuous. Sourced from Process NB.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	3.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FPN330 / FPN330A	
PD	Total Device Dissipation	1.0	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

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NPN Low Saturation Transistor (continued)

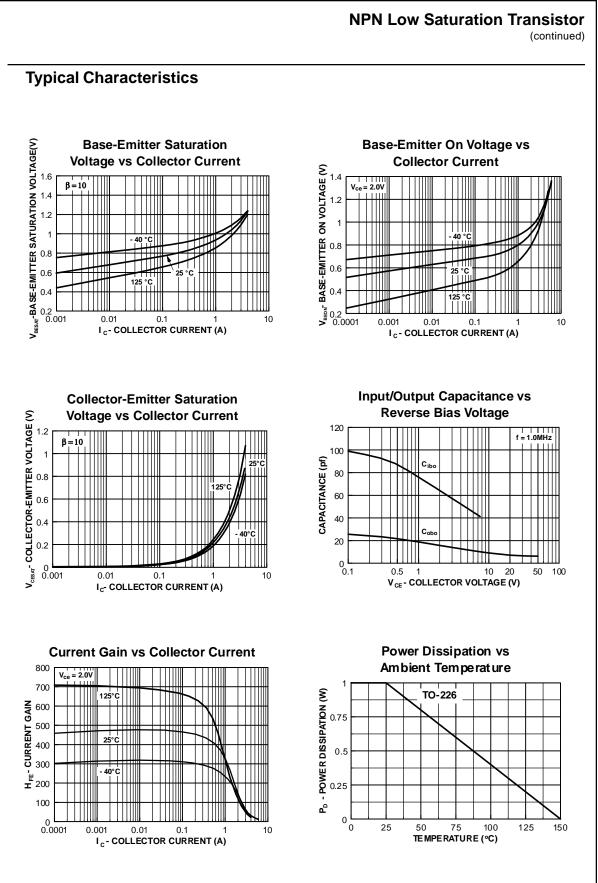
Symbol	Parameter	Test Conditions	Min	Мах	Units
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	30		V
ВV _{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu A, \ I_{\rm E} = 0$	50		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \ \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$ $V_{CB} = 30 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$		100 10	nA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		100	nA

h _{FE}	DC Current Gain	$I_{C} = 100 \text{ mA}, V_{CE} = 2.0 \text{ V}$	330	100		
			330A	250		
		$I_{C} = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$		120		
		$I_{C} = 2.0 \text{ A}, V_{CE} = 2.0 \text{ V}$		50		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1.0 \text{ A}, I_{\rm B} = 100 \text{ mA}$	330		500	mV
			330A		450	mV
		$I_{\rm C} = 2.0 \text{ A}, I_{\rm B} = 200 \text{ mA}$			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1.0 A, I _B = 100 mA			1.25	V
V _{BE(on)}	Base-Emitter Saturation Voltage	$I_{C} = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$			1.0	V

SMALL SIGNAL CHARACTERISTICS

Cobo	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		30	pF
FT	Transition Frequency	I _C = 100 mA, V _{CE} = 5.0 V, f = 100 MHz	100		MHz

*Pulse Test: Pulse Width \leq 300 $\mu s, \, Duty \, Cycle \leq 2.0\%$



FPN330 / FPN330A

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